

Title (en)

PROCESS FOR MANUFACTURING AN ACTIVE MATRIX DISPLAY.

Title (de)

HERSTELLUNGSVERFAHREN FÜR AKTIVMATRIX-BILDSCHIRM.

Title (fr)

PROCEDE DE FABRICATION D'UN AFFICHAGE A MATRICE ACTIVE.

Publication

**EP 0647354 A1 19950412 (EN)**

Application

**EP 93910769 A 19930426**

Priority

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- US 9303854 W 19930426

Abstract (en)

[origin: DE4310640C1] The mfg. system for a Si:H thin-film transistors with storage capacitors uses 2 sputtered and structured chrome surfaces (11,12) applied to a substrate (10), respectively providing a row line nad a gate contact for each thin film transistor (19) and the base electrode of the storage capacitor. A gate isolator (13) and a Si:H intrinsic and doped semiconductor layers (14,15) are then applied, with wet or dry etching of the semiconductor layers via a metallisation mask. An indium-tin oxide is deposited and structured to form image print electrodes with a further metallisation for the matrix columns and etching of the metallisation mask using the indium-tin oxide as the mask. A transparent passivation layer is then applied. USE - For simplified mfr. of liquid crystal display screen.

IPC 1-7

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IPC 8 full level

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